

*Cited Reference 1***PATENT ABSTRACTS OF JAPAN**

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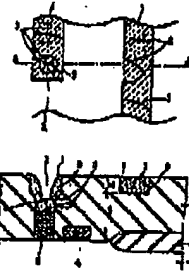
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YOSHIOKA NOBUYUKI**(54) SEMICONDUCTOR DEVICE AND ITS MANUFACTURE****(57)Abstract:****PURPOSE:** To form an aluminum wiring of high electromigration resistance.**CONSTITUTION:** An aluminum wiring 1 is buried in a trench 9 formed in an interlayer insulating film 8 on a silicon substrate 7, and subjected to annealing by laser scanning. As the result, the periphery of the aluminum wiring 1 is surrounded by the interlayer insulating film 8 serving as a thermal insulator, so that heat is not dissipated from the periphery of the aluminum wiring, and crystallization from the periphery can be prevented. Thereby crystal grains of aluminum can be grown to be large. On account of the increase of crystal grain diameter, the density of grain boundary generating aluminum atom migration is decreased, and the aluminum wiring of high reliability can be formed.**LEGAL STATUS**

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